

# isc N-Channel Mosfet Transistor

## **STFW69N65M5**

PD

- FEATURES
- Drain Current I<sub>D</sub>= 58A@ T<sub>C</sub>=25℃
- · Drain Source Voltage-
  - : V<sub>DSS</sub>= 650V(Min)
- · Fast Switching Speed
- 100% avalanche tested
- · Minimum Lot-to-Lot variations for robust device performance and reliable operation

## APPLICATIONS

SYMBOL

VDSS

 $V_{\text{GS}}$ 

 $I_D$ 

 $I_{DM}$ 

 $P_{tot}$ 

Tj

T<sub>stg</sub>

Switching applications

## ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

Drain-Source Voltage

Gate-Source Voltage

Pulse Drain Current

Total Dissipation@Tc=25°C

Storage Temperature Range

PARAMETER

Drain Current-continuous@ Tc=25°C

Max. Operating Junction Temperature

	pin 1.Gate 2.Drain 3.Source 1 2 3 TO-3PML package
UNIT	
V	
V	
A	
A	
W	mm   DIM MIN MAX   A 19.90 20.10
°C	B 15.75 16.10 C 5.50 5.70 D 0.90 1.10

	~	10.00	20.10
	В	15.75	16.10
- 1	С	5.50	5.70
	D	0.90	1.10
0	F	3.30	3.50
	G	2.90	3.20
	Н	5.90	6.10
	J	0.595	0.70
1	Κ	21.10	22.50
	L	1.90	2.25
	N	10.80	11.00
	Q	4.90	5.10
	R	3.75	3.95
1	S	3.20	3.60
Ē	U	9.90	10.10
	Y	4.20	4.90
	Ζ	1.90	2.10

SYMBOL	PARAMETER

THERMAL CHARACTERISTICS

R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	1.58

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1

VALUE

650

 $\pm 25$ 

58

232

79

150

-55~150

MAX

°C

UNIT

°C/W



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#### **ELECTRICAL CHARACTERISTICS**

#### $T_{\text{C}}\text{=}25\,^{\circ}\!\!\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	МАХ	UNIT
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0; I <sub>D</sub> = 1mA	650			V
V <sub>GS</sub> (th)	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> ; I <sub>D</sub> =250µA	3		5	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> = 29A			45	mΩ
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> = ±25V;V <sub>DS</sub> = 0			±100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = Max rating			1	μA
		V <sub>Ds</sub> = Max rating; T <sub>c</sub> =125℃			100	
V <sub>SD</sub>	Diode Forward On-Voltage	I <sub>S</sub> = 58A ;V <sub>GS</sub> = 0			1.5	V

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